





30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	Package	I _{D max} T _A = +25°C
-30V	72mΩ @ V _{GS} = -10V	SOT-23	-3.9A
-307	85mΩ @ V _{GS} = -4.5V	501-23	-3.6A

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Description and Applications

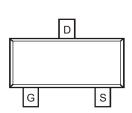
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Mechanical Data

- Case: SOT23 (Standard)
- Case Material: Molded Plastic.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminals: Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

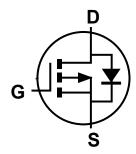


Top View



SOT23

Top View Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

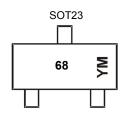
Part Number	Case	Packaging
DMP3068L-7	SOT23 (Standard)	3,000/Tape & Reel
DMP3068L-13	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



68 = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: B = 2014) M or \overline{M} = Month (ex: 9 = September)

Date Code Kev

Year	2014		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	В		ı	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±12	V
Drain Current (Note 6) / 10) /	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.3 -2.6	Α
Drain Current (Note 6) V _{GS} = -10V	T _A = +25°C T _A = +70°C	I _D	-3.9 -3.2	Α	
Pulsed Drain Current (Pulse width ≤10µS, Duty	Cycle ≤1%)		I _{DM}	-18	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	0.7	W		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	182	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ heta JA}$	133	C/VV	
Total Power Dissipation (Note 6)	P_{D}	1.2	W		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	103	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ heta JA}$	75	C/VV	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

Notes:

^{5.} Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.



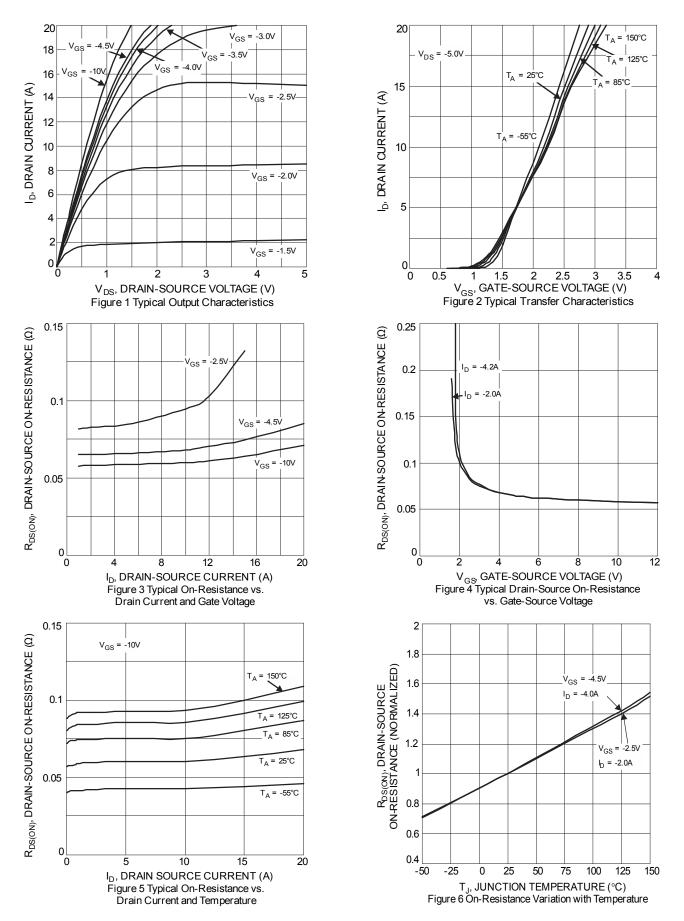
Electrical Characteristics (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V$, $I_D = -250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±12V, V _{DS} = 0V		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-1.3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$		
Static Drain-Source On-Resistance	R _{DS (ON)}	_	57 64 80 107	72 85 120 165	mΩ	$V_{GS} = -10V$, $I_D = -4.2A$ $V_{GS} = -4.5V$, $I_D = -4.0A$ $V_{GS} = -2.5V$, $I_D = -2.0A$ $V_{GS} = -1.8V$, $I_D = -1.0A$		
Diode Forward Voltage	V_{SD}	_	_	-1.2	V	V _{GS} = 0V, I _S = -1.0A		
DYNAMIC CHARACTERISTICS (Note 8)				•				
Input Capacitance	C _{iss}		708	_	pF			
Output Capacitance	Coss		57	_	pF	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1.0MHz$		
Reverse Transfer Capacitance	C _{rss}	_	47	_	pF			
Gate Resistance	R _G	_	14	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz		
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	7.3	_	nC	V _{DS} = -15V, I _D = -4A		
Total Gate Charge (V _{GS} = -10V)	Q_{G}	_	15.9	_				
Gate-Source Charge	Q _{GS}	_	1.2	_	nC	V _{DS} = -15V, I _D = -4A		
Gate-Drain Charge	Q_{GD}	_	1.7	_				
Turn-On Delay Time	t _{d(on)}	_	3.5	_				
Rise Time	t _r		15.8	_		V _{DS} = -15V, V _{GS} = -10V,		
Turn-Off Delay Time	t _{d(off)}		70.3	_	ns	$I_D = -4A, R_G = 6.0\Omega$		
Fall Time	tf		33.9	_				

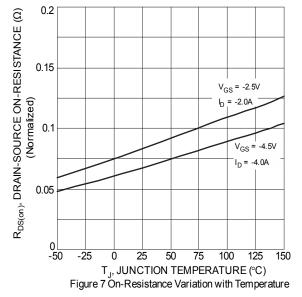
Notes:

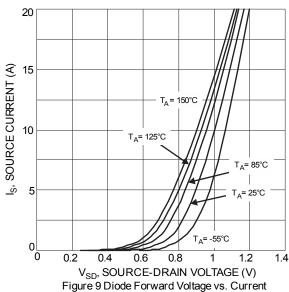
^{7.} Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

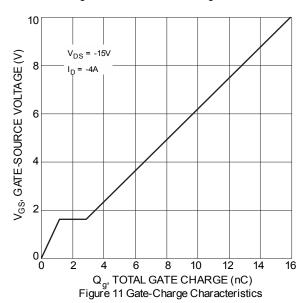












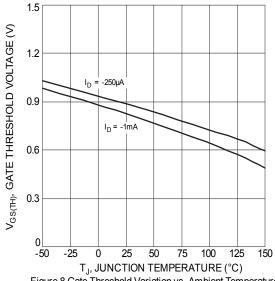
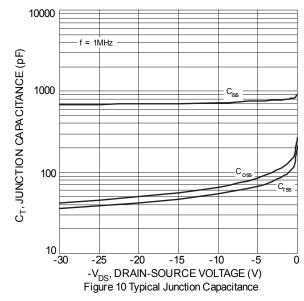
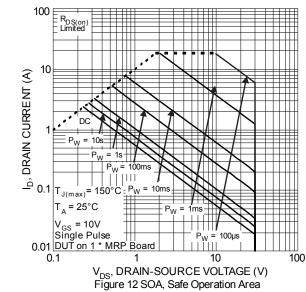
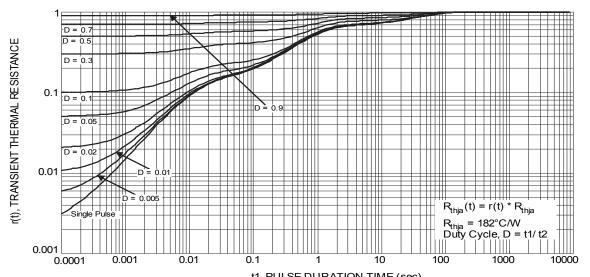


Figure 8 Gate Threshold Variation vs. Ambient Temperature









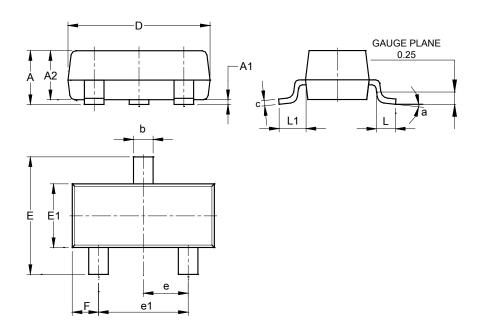
t1, PULSE DURATION TIME (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)

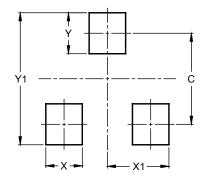


SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°	-				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Υ	0.9				
Y1	2.9				



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